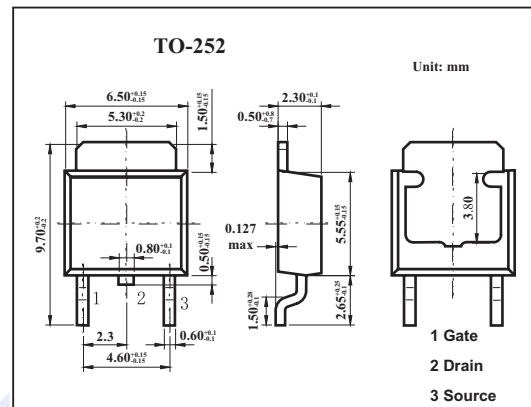
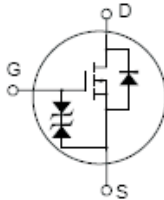


Silicon N-Channel MOSFET 2SK2084S

■ Features

- Low on-resistance
- High speed switching
- Low drive current
- Suitable for Switching regulator, DC - DC converter



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage	V _{DSS}	20	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	7	A
Power dissipation	P _D	20	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain cut-off current	I _{DSS}	V _{DS} =16V, V _{GS} =0			100	μA
Gate leakage current	I _{GSS}	V _{GS} =±16V, V _{DS} =0			±10	μA
Gate to source cutoff voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	1.0		2.5	V
Forward transfer admittance	Y _{fs}	V _{DS} =10V, I _D =4A	5	9		S
Drain to source on-state resistance	R _{Ds(on)}	V _{GS} =10V, I _D =4A		0.04	0.053	Ω
		V _{GS} =4V, I _D =4A		0.058	0.075	Ω
Input capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0, f=1MHZ		800		pF
Output capacitance	C _{oss}			680		pF
Reverse transfer capacitance	C _{rss}			165		pF
Turn-on delay time	t _{d(on)}	I _D =4A, V _{GS(on)} =10V, R _L =5Ω		15		ns
Rise time	t _r			60		ns
Turn-off delay time	t _{d(off)}			100		ns
Fall time	t _f			80		ns